TDM Photonic Network using Deposited Materials

ROBERT HENDRY, GILBERT HENDRY, KEREN BERGMAN

LIGHTWAVE RESEARCH LAB COLUMBIA UNIVERSITY

HPEC 2011

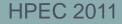
lightwave research laboratory COLUMBIA UNIVERSITY

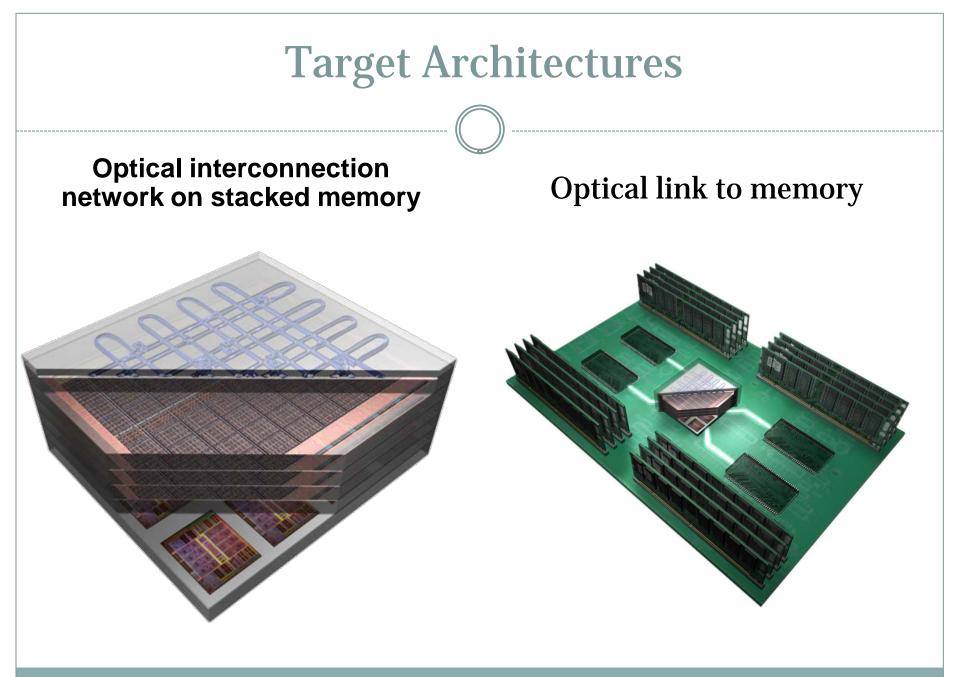
Motivation for Silicon Photonics

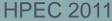
- Performance scaling becoming extremely difficult
 - Data movement cost increasingly expensive
 - On/off-chip communication bandwidth limited

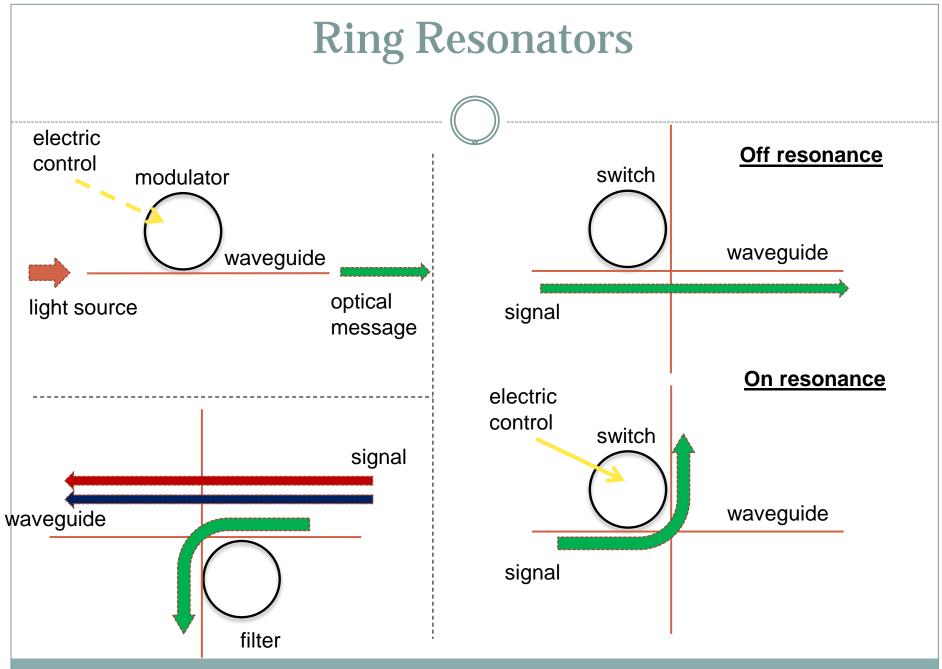
• Photonics offers:

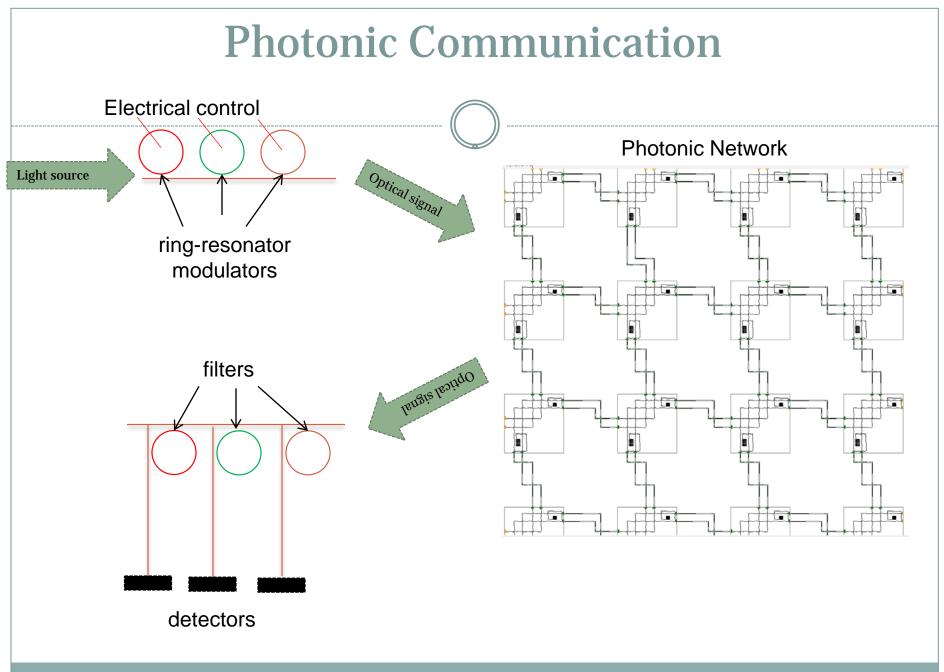
- Higher bandwidth density
 - **×** High datarate and parallel wavelengths
- Low operating power
- Low latency

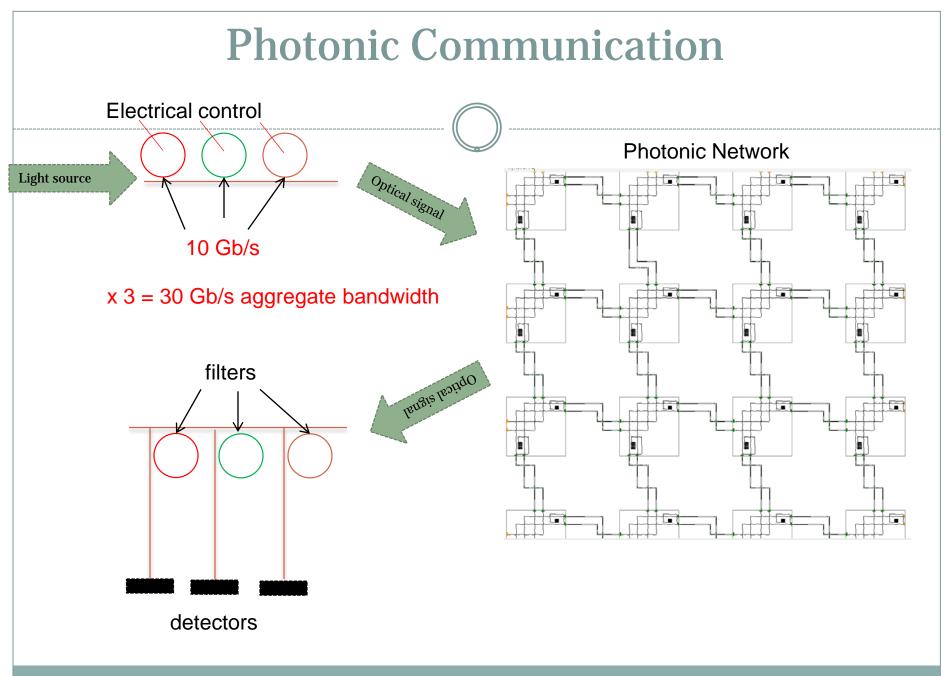


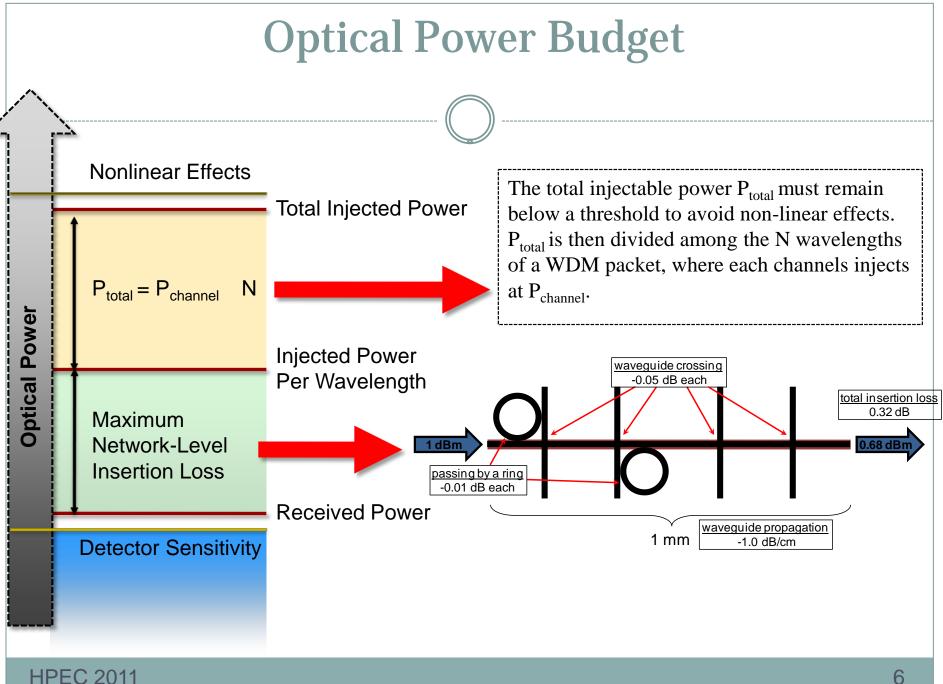












Silicon Photonics Technologies

Material	Propagation Loss
Crystalline Silicon	1.7 dB/cm [Xia et al. 2007]

Crystalline Silicon

- Best electrical and optical properties
- Unable to deposit

Silicon Photonics Technologies

Material	Propagation Loss
Crystalline	1.7 dB/cm
Silicon	[Xia et al. 2007]
Polycrystalline	6.45 dB/cm
Silicon	[Fang et al. 2008]

- Crystalline Silicon
 - Best electrical and optical properties
 - Unable to deposit
- Polycrystalline Silicon

 Can deposit
 - Very lossy

Silicon Photonics Technologies

Material	Propagation Loss
Crystalline	1.7 dB/cm
Silicon	[Xia et al. 2007]
Polycrystalline	6.45 dB/cm
Silicon	[Fang et al. 2008]
Silicon Nitride	0.1 dB/cm [Shaw et al. 2005] [Gondarenko et al. 2009]

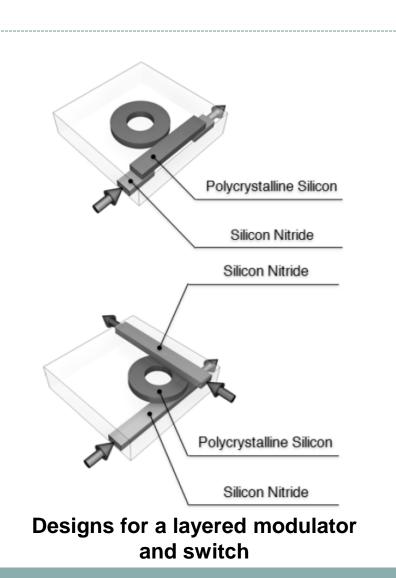
- Crystalline Silicon
 - Best electrical and optical properties
 - Unable to deposit
- Polycrystalline Silicon

 Can deposit
 - Very lossy
- Silicon Nitride

 Very low loss
 - Can deposit
 - Not useful active devices

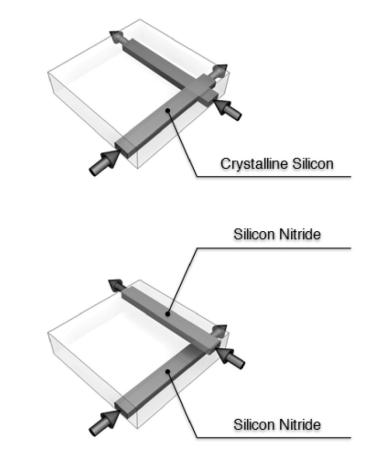
Poly-Si / SiN Combination approach

- We can use silicon nitride and polycrystalline silicon in combination
 - SiN for non-active wave guides
 - Poly-Si for active devices (e.g. ring-resonator based switch)





Poly-Si / SiN Combination approach



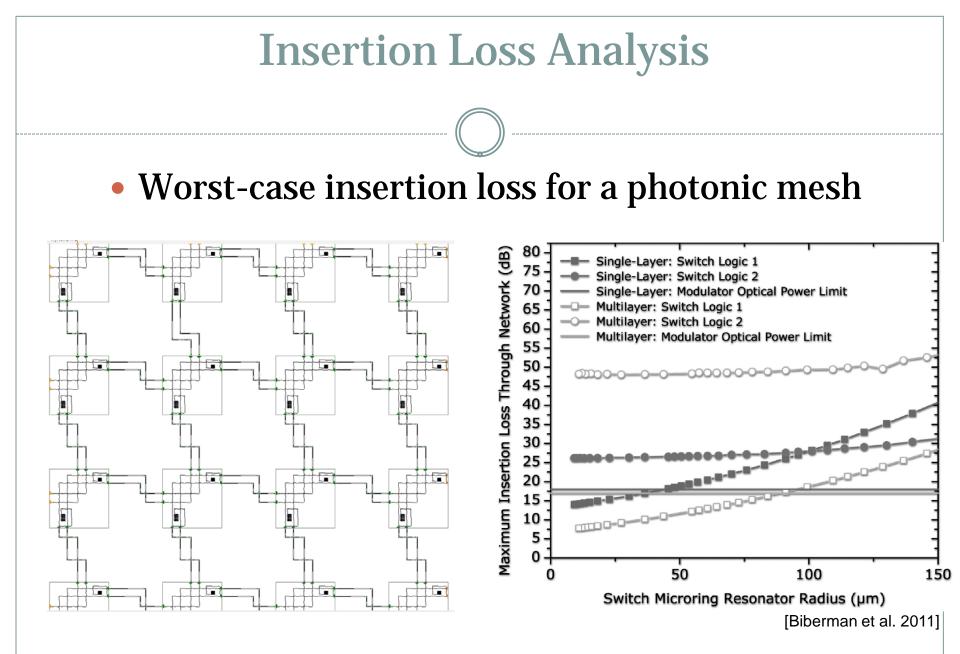
Waveguide crossings eliminated

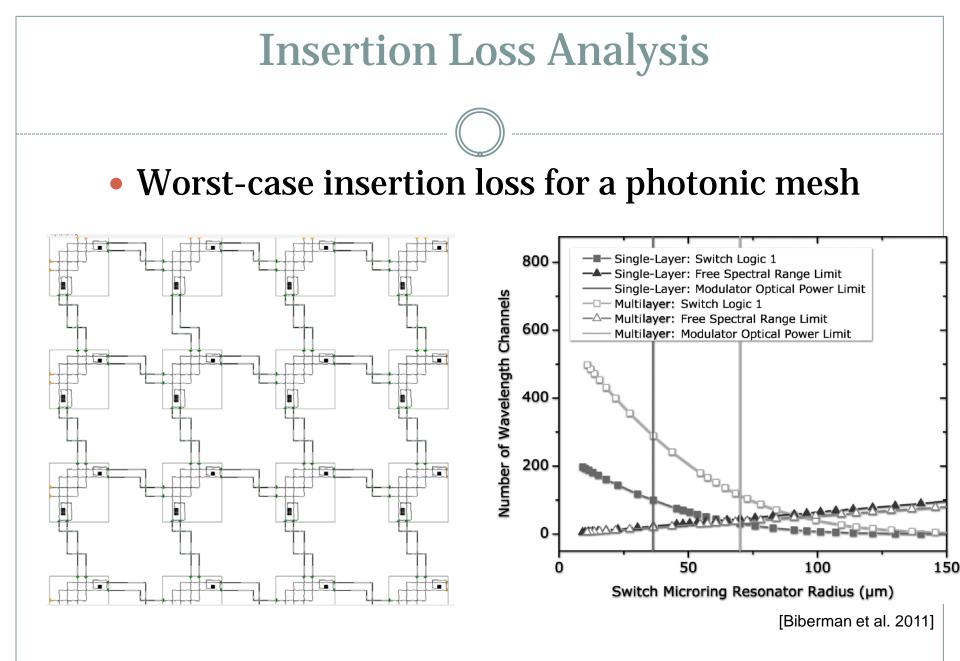
 Insertion loss, crosstalk both incurred heavily in waveguide crossings

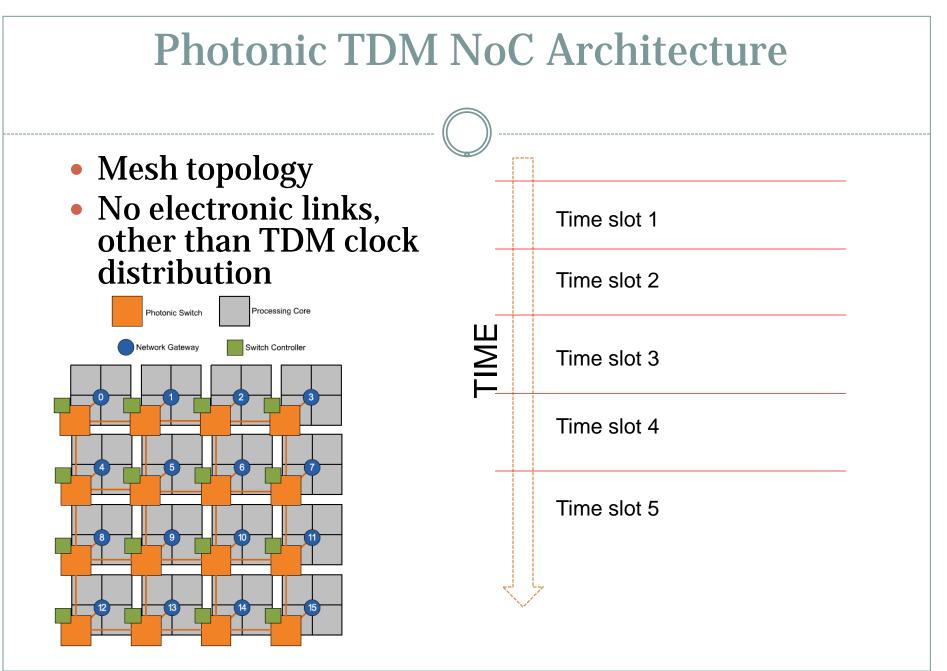
However, .1 dB insertion loss per vertical coupling [Sun et al. 2008]

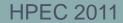
Single-Layer

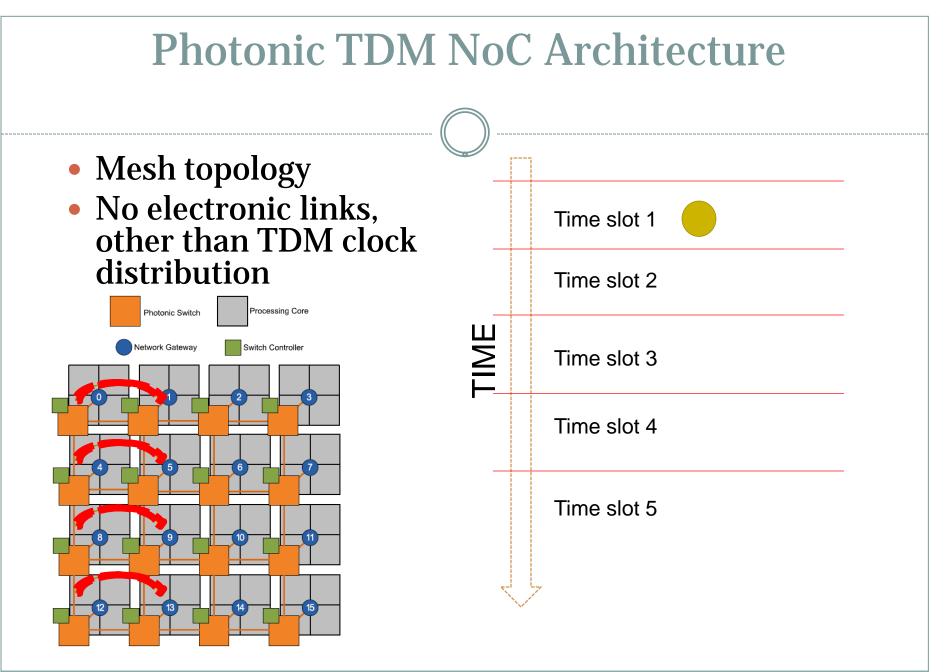
3D-Integrated

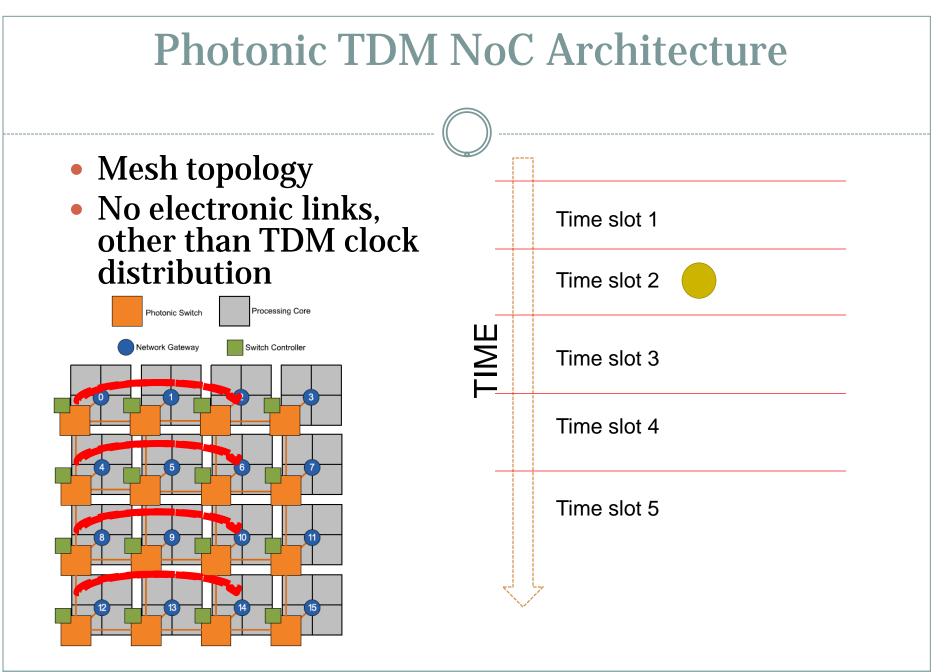


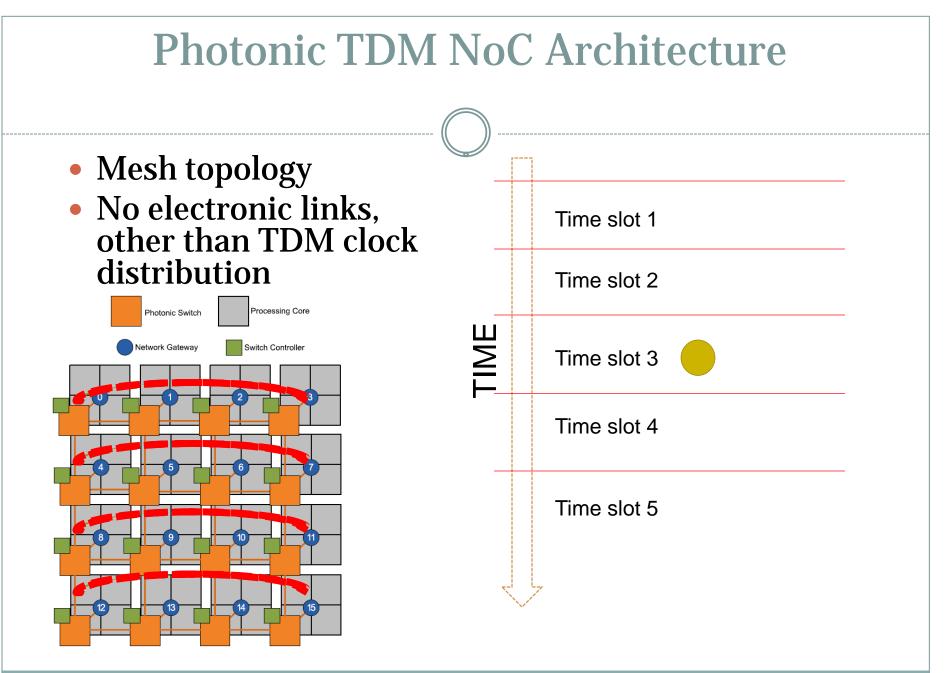




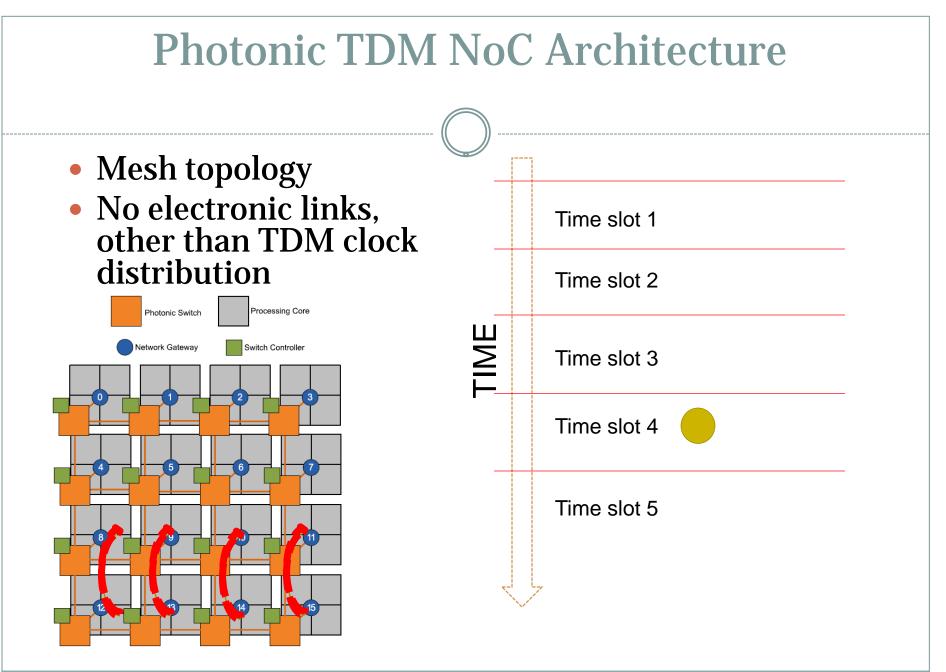


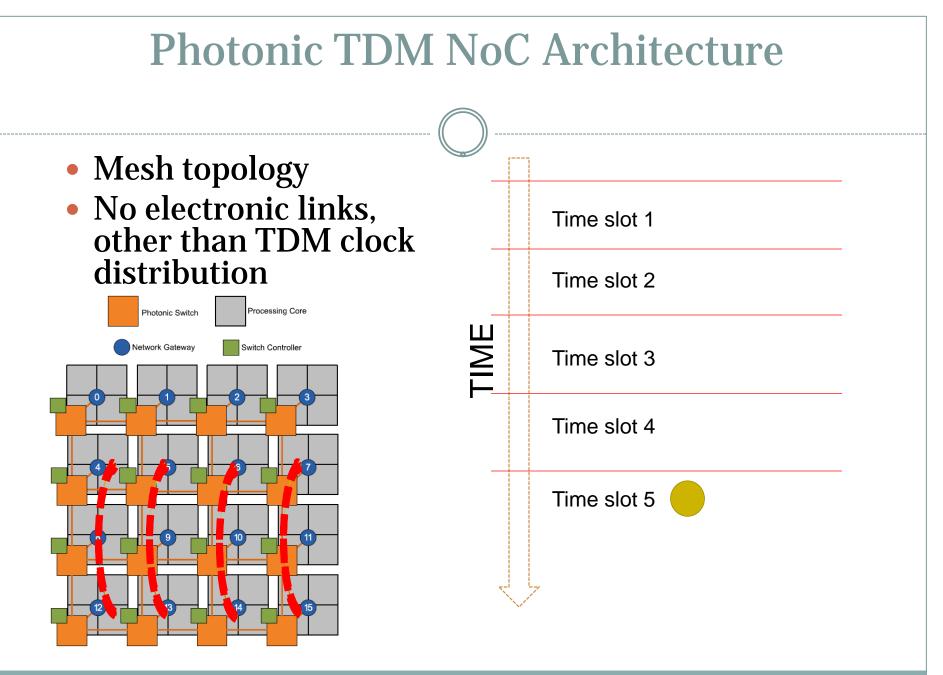


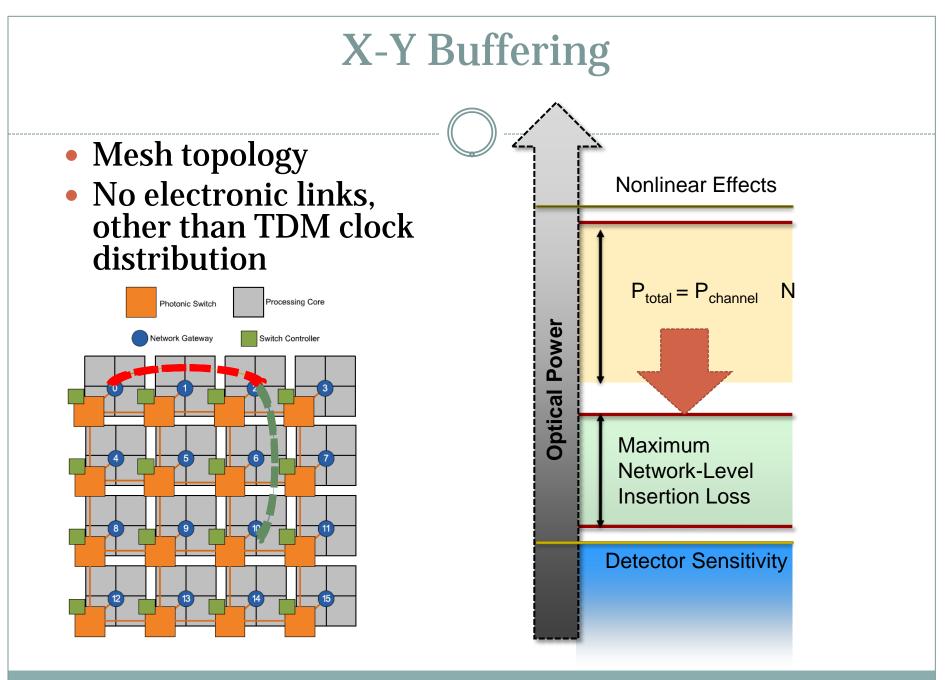


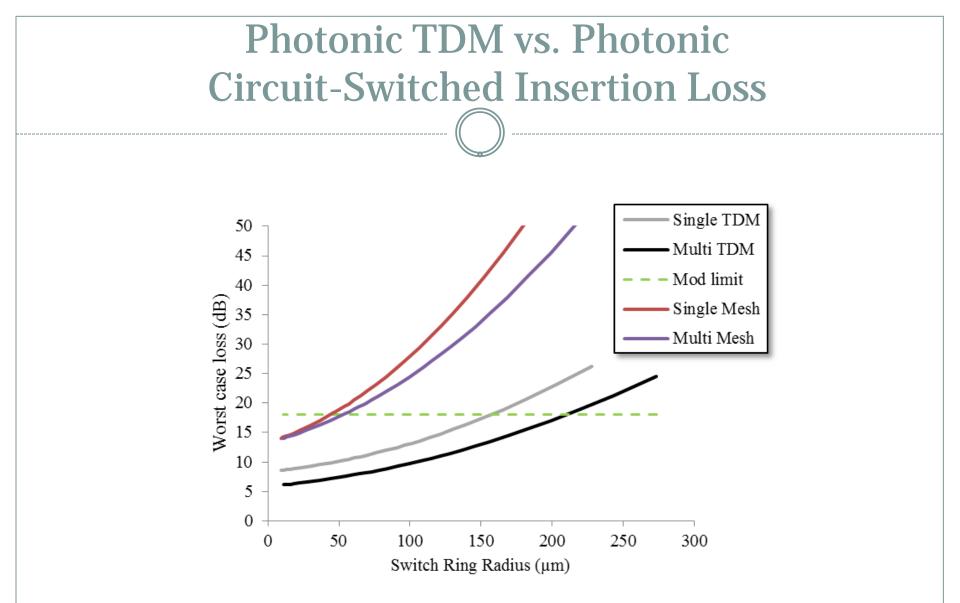


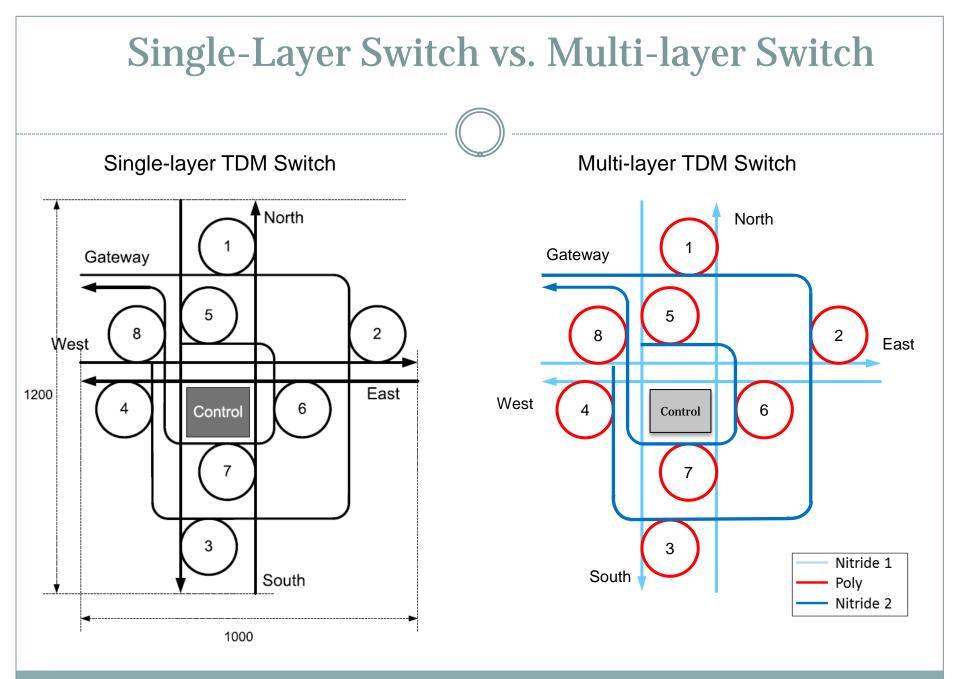


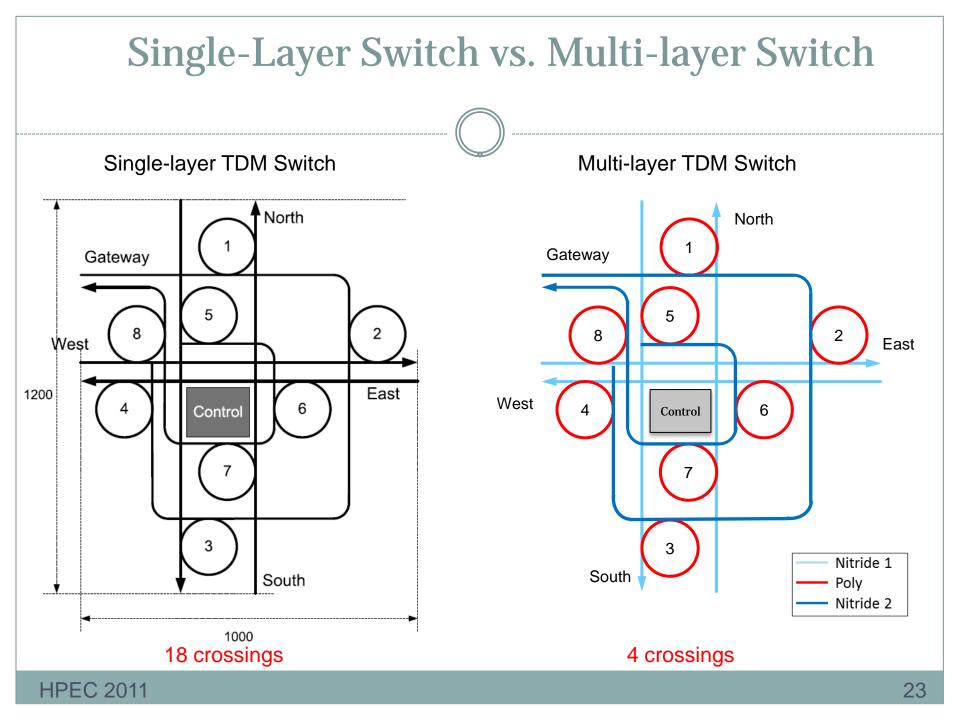


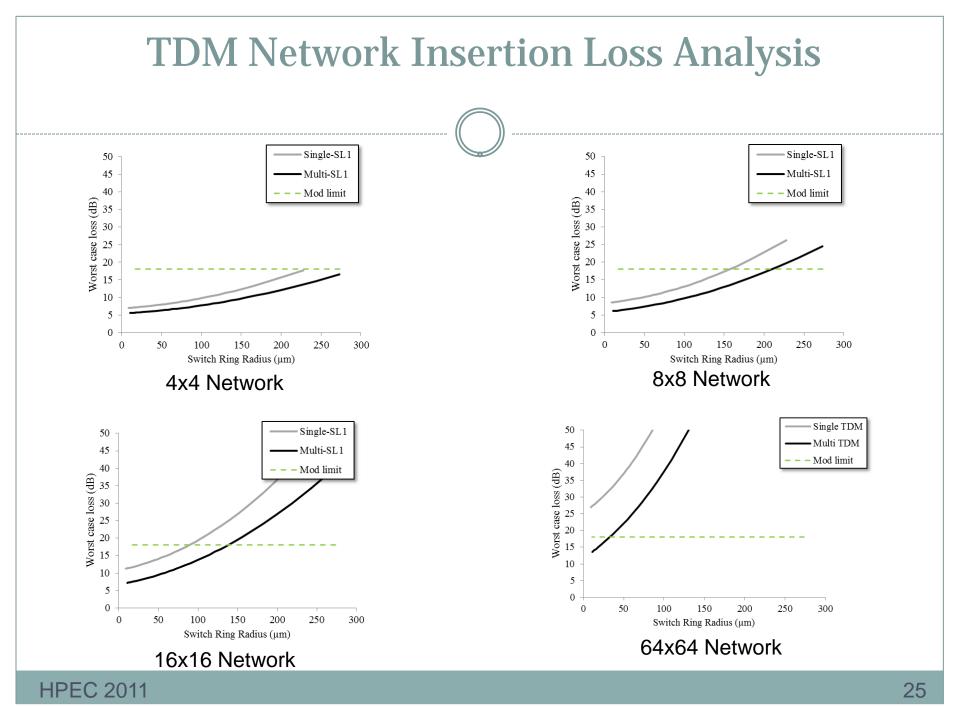












Maximum Bandwidth (# of Wavelengths) 800 1200 Single-SL1 -Single-SL1 700 1000 -Multi-SL1 Multi-SL1 Number of wwavelengths 00 00 00 008 Single FSR Single FSR Multi FSR -Multi FSR 200 100 0 0 50 250 0 50 100 150 200 Switch Ring Radius (µm) 250 300 100 150 200 Switch Ring Radius (µm) 300 8x8 Network 4x4 Network 160 700 -Single-SL1 -Single-SL1 140 600 Multi-SL1 Number of wwavelengths 00 00 00 00 00 00 00 -Multi-SL1 Number of wwavelengths 000 000 000 000 000 Single FSR Single FSR -Multi FSR -Multi FSR 100 20 0 0

0

50

Switch Ring Radius (µm)

64x64 Network

16x16 Network

Switch Ring Radius (µm)

0

HPEC 2011

50

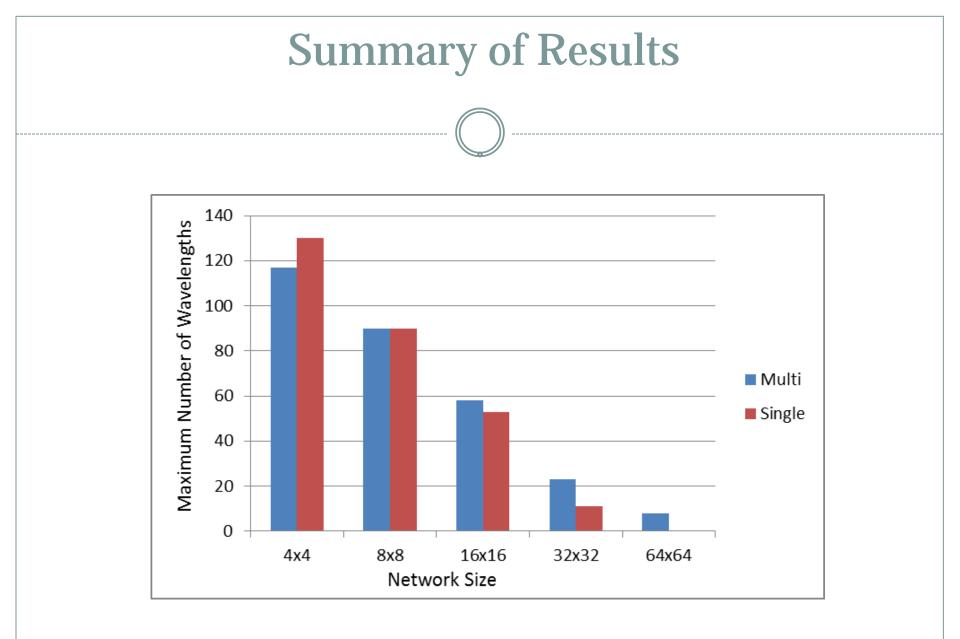
250

300

26

300

250



Conclusions

- Poly-Silicon and Silicon Nitride in conjunction are a good choice of materials for photonic interconnection networks
 - o Low-loss
 - = more wavelengths = higher bandwidth
- We've shown that our best network, when at large scale, can be improved with a multi-layer implementation
- Future work: We expect the elimination of waveguide crossings to significantly reduce crosstalk across a wide variety of network architectures